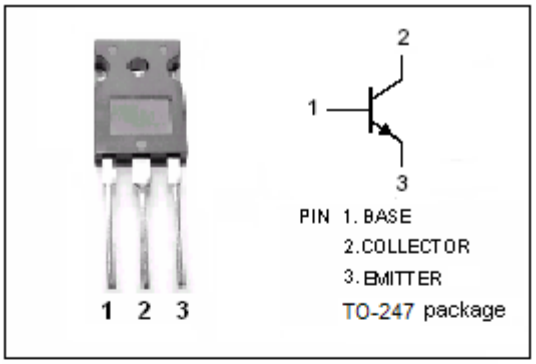
isc Silicon NPN Power Transistor 2SD2236

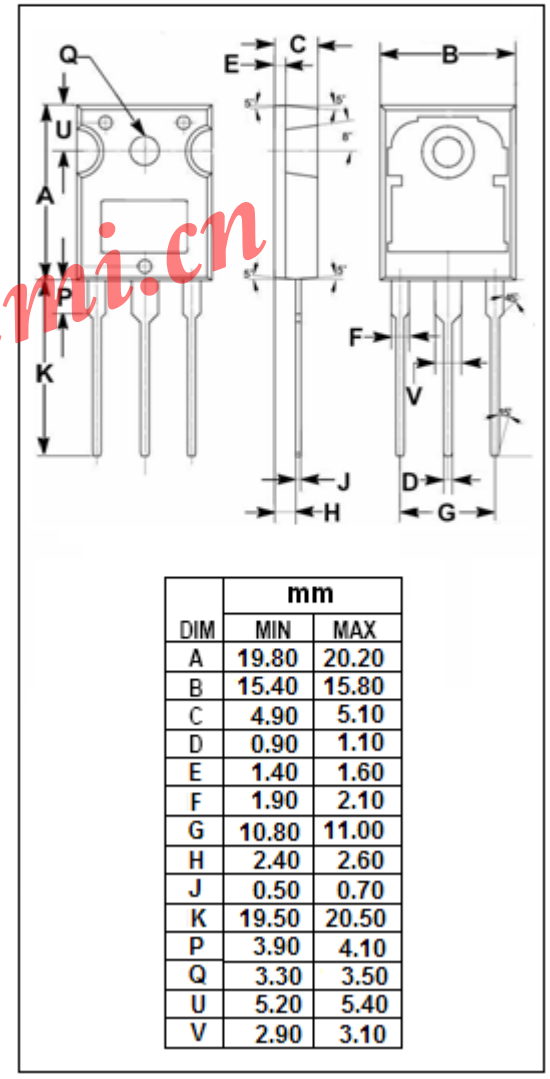


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 100V(Min.)
- Wide Area of Safe Operation
- Complement to Type 2SB1477

APPLICATIONS

- Designed for driver and general purpose applications.



DIM	mm MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
P_C	Collector Power Dissipation @ T_C=25℃	60	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Beakdown Voltage	I_C= 10mA; I_B= 0	100			V
$V_{(BR)CBO}$	Collector-Base Beakdown Voltage	I_C= 50μA; I_E=0	100			V
$V_{(BR)EBO}$	Emitter-Base Beakdown Voltage	I_E= 50μA; I_C=0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			10	μA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 5V	60		320	

◆ **h_{FE} Classifications**

D	E	F
60-120	100-200	160-320